



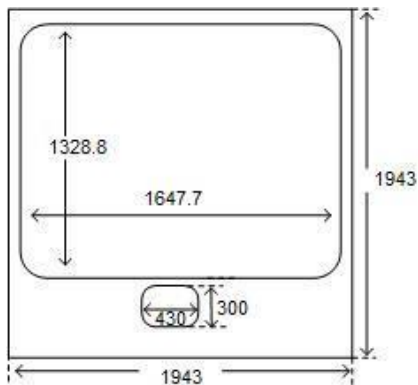
NDM60S2W

Fast Recovery N-channel MOSFET (Ultra Low Trr)

Rev.1.0

2021/9/27

Mechanical Data



Item	Information	
Chip Size	1883*1883	um ²
Gate Pad Size	430*300	
Source Pad Size	1647.7*1328.8	
Scribe Line Width	60	um
Wafer Thickness	300	
Wafer diameter	150	mm
Source Metallization	Al, Si, Cu	
Drain Metallization	Ti, Ni, Ag	
Reject Ink Dot Size	ø 10mil	
Recommended Storage Environment	Store in original container, in dry nitrogen, (6 months at an ambient temperature of 23°C+/-3°C)	

Electrical characteristics in C/P test @Tj=25°C

Parameter	Description	Min.	Typ.	Max.	Unit	Test Condition
V _{(BR)DSS}	Drain-Source Breakdown Voltage	600	-	-	V	V _{GS} =0V, I _D =250uA
R _{DS(ON)}	Static Drain-Source On-Resistance	-	4.5	4.8	Ω	V _{GS} =10V, I _D =1A
V _{GS(th)}	Gate Threshold Voltage	1.5	-	4	V	V _{GS} =V _{GS} , I _D =250uA
I _{DSS}	Drain-to-Source Leakage Current	-	-	0.3	uA	V _{DS} =600V, V _{GS} =0V
I _{GSS}	Gate-Body Leakage Current	-	-	0.3	uA	V _{DS} =0V, V _{GS} =±30V

Source to drain diode ratings characteristics

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
I _S	Continuous source current	Integral reverse p-n Junction current	-	-	5.5	A
I _{SM}	Pulsed source current		-	-	22	A
V _{SD}	Diode forward voltage drop	I _S =1.0A, V _{GS} =0V	-	0.9	1.2	V
T _{rr}	Reverse recovery time	I _S =1A, V _{DD} =30V V _{GS} =0V, dI _F /dt=50A/us	-	65		ns